BLW77

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW77** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

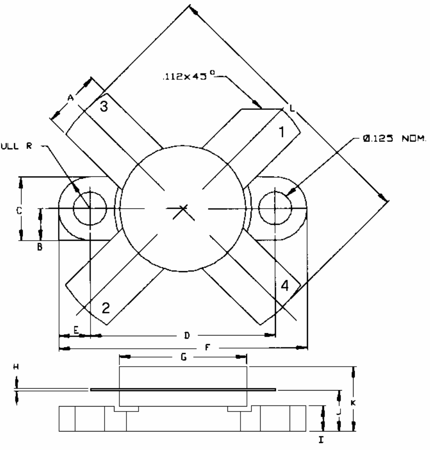
FEATURES:

- **P_G** = 12 dB min. at 15-30 W/1.6-28 MHz
- Common Emitter
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{CB}	70 V
V_{CE}	35 V
P_{DISS}	245 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.71 °C/W

PACKAGE STYLE .500 4L FLG



1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.125/3,18	
C	.245/6,22	.255/6,48
D	.720/18,28	.730/18,54
E	.125/3,18	
F	.970/24,64	.980/24,89
G	.495/12,57	.505/12,83
H	.003/0,08	.007/0,18
I	.090/2,29	.110/2,79
J	.160/4,06	.175/4,45
K		.280/7,11
L		1.050/26,67

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 100 mA	35			**V**
BV_{CES}	I_C = 50 mA	70			**V**
BV_{EBO}	I_E = 20 mA	3.0			**V**
I_{CES}	V_E = 35 V			20	**mA**
h_{FE}	V_{CE} = 5.0 V I_C = 7.0 A	15		80	**---**
C_c	V_{CB} = 28 V f = 1.0 MHz		225		**pF**
G_P **d_3** **η**	V_{CE} = 28 V $I_{C(ZS)}$ = 0.1 A f = 1.6-28 MHz P_L = 15-130 W (PEP)	12 37.5		 -30 	**dB** **dB** **%**